## Amendments to the Specification:

Please replace the paragraph that begins at page 7, line 12 with the following amended paragraph:

The substrate 100 has a p-doping of about 3 x 10<sup>15</sup> 1/cm<sup>3</sup>. On a surface 102 of the substrate 100 a gate structure 104 is formed including a gate polysilicon 106 and a gate oxide 108 arranged between the gate polysilicon 106 and the substrate 100. Within the substrate 100 further an n<sup>+</sup>-source area 110 and an n<sup>+</sup>-drain area 112 is formed. The regions 112a, 112b, 112c indicate drain area regions with different doping concentrations. Below the gate oxide 108 a laterally diffused channel area 114 is formed comprising a p-doping in the area of about 2 x 10<sup>17</sup> 1/cm<sup>3</sup>. The source area 110 and the drain area respectively comprise n-dopings of about 2 x 10<sup>20</sup> 1/cm<sup>3</sup>.

Please replace the paragraph that begins at page 9, line 27 with the following amended paragraph:

Fig. 2 Curve 2 shows the course of the input characteristic line after the additional pregion 118 was implanted into the LDD area 116. As it may be seen, hereby the characteristic line is lowered, as due to the p-region 118 the resistance in the LDD area 116 is increased and so the drain current compared to the LDD area correspondingly decreases without an additional p-region 118 (curve 1).